TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# 2SC5066FT

# VHF~UHF Band Low Noise Amplifier Applications

Unit: mm

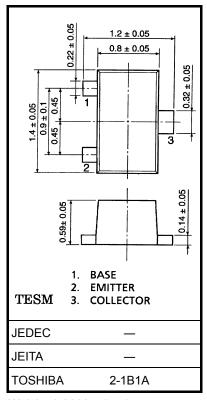
- Low noise figure, high gain.
- NF = 1.1dB,  $|S_{21e}|^2 = 12dB$  (f = 1 GHz)

# Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	20	V
Collector-emitter voltage	$V_{CEO}$	12	V
Emitter-base voltage	$V_{EBO}$	3	>
Base current	lΒ	15	mA
Collector current	IC	30	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	<b>−55~125</b>	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.0022 g (typ.)

# Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA	5	7	_	GHz
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA, f = 500 MHz	_	17	_	- dB
	S <sub>21e</sub>   <sup>2</sup> (2)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA, f = 1 GHz	8.5	12	_	
Noise figure	NF (1)	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ mA}, f = 500 \text{ MHz}$	_	1	_	dB
	NF (2)	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ mA}, f = 1 \text{ GHz}$	_	1.1	2.0	uБ

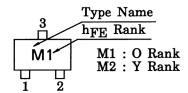
#### **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0	_	_	1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μΑ
DC current gain	h <sub>FE</sub> (Note 1)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA	80	_	240	
Output capacitance	C <sub>ob</sub>	$V_{CB} = 5 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.7	_	pF
Reverse transfer capacitance	C <sub>re</sub>		_	0.45	0.9	pF

Note 1: hFE classification O: 80~160, Y: 120~240

Note 2: C<sub>re</sub> is measured by 3 terminal method with capacitance bridge.

# Marking



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20070701-EN GENERAL

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